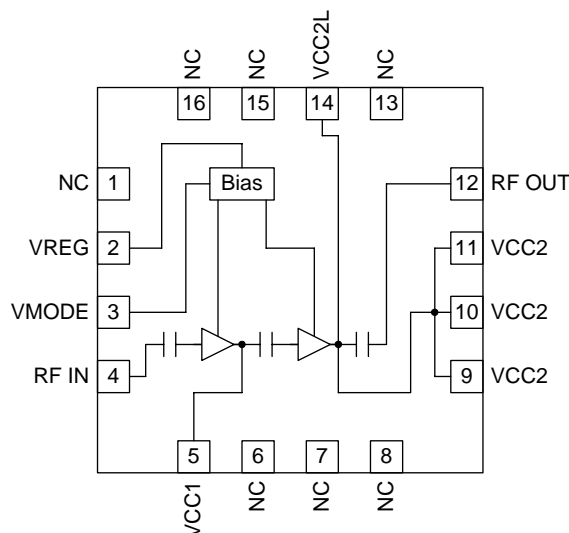


Features

- Input Internally Matched at 50Ω
- Output Internally Matched
- 23% Linear Efficiency at 19dBm
- HSDPA Compliant at 26.5dBm
- 40% Linear Efficiency at 28dBm
- -40dBc ACLR at 5MHz
- 18mA Idle Current in LPM

Applications

- 3V Band V UMTS Cellular Handset
- 3V Band VIII UMTS Cellular Handset
- Spread-Spectrum System



Functional Block Diagram

Product Description

The RF6266 is a high-power, high-efficiency linear amplifier module specifically designed for 3V handheld systems. The device is manufactured on an advanced third generation GaAs HBT process, and was designed for use as the final RF amplifier in 3V UMTS handheld digital cellular equipment, spread-spectrum systems, and other applications in the 824MHz to 915MHz frequency range. The RF6266 has a digital control pin which when enabled will allow the amplifier to operate up to 19dBm output power with reduced current consumption. The low power mode current consumption can be reduced by more than 50% that of a standard power amplifier. The RF6266 is assembled in a 16-pin, 3mmx3mm, QFN package.

Ordering Information

| | |
|----------------|--|
| RF6266 | 3V 850MHz/900MHz Linear Power Amplifier Module |
| RF6266PCBA-41X | Fully Assembled Evaluation Board |

Optimum Technology Matching® Applied

- | | | | |
|--|--------------------------------------|-------------------------------------|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

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for more information.**